## Xing-Zhao Liu

List of Publications by Year in descending order

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623734 501196 40 804 14 28 citations g-index h-index papers 40 40 40 1113 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Photoelectric properties of $\hat{l}^2$ -Ga2O3 thin films annealed at different conditions. Rare Metals, 2022, 41, 1375-1379.	7.1	9
2	Dilute-selenium alloying: A possible perspective for achieving p-type conductivity of $\hat{l}^2$ -gallium oxide. Journal of Alloys and Compounds, 2022, 891, 161969.	5.5	6
3	van der Waals growth of PbSe thin films on graphene and Bi2Se3. Vacuum, 2022, 201, 111043.	3.5	3
4	Characterization and performance of graphene–PbSe thin film heterojunction. Rare Metals, 2021, 40, 219-224.	7.1	11
5	Investigation on band alignment of Bi2Se3–PbSe heterojunction. Applied Physics Letters, 2021, 118, 162101.	3.3	2
6	Fabrication of Topological Insulator Bi 2 Se 3 â^'PbSe Heterojunction Photodetector for Infrared Detection. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100406.	2.4	3
7	Two-dimensional MoSe2/graphene heterostructure thin film with wafer-scale continuity via van der Waals epitaxy. Chemical Physics Letters, 2020, 755, 137762.	2.6	3
8	Pyrochlore oxide Y2Hf2O7 thin films for solar-blind UV detectors. Optical Materials, 2020, 105, 109837.	3.6	1
9	High performance photodetectors constructed on atomically thin few-layer MoSe2 synthesized using atomic layer deposition and a chemical vapor deposition chamber. Journal of Alloys and Compounds, 2019, 785, 951-957.	5.5	21
10	Layer-controlled synthesis of wafer-scale MoSe2 nanosheets for photodetector arrays. Journal of Materials Science, 2018, 53, 8436-8444.	3.7	38
11	Synthesis of few-layer 2H-MoSe <sub>2</sub> thin films with wafer-level homogeneity for high-performance photodetector. Nanophotonics, 2018, 7, 1959-1969.	6.0	41
12	Characterization of Molybdenum Oxide Thin Films Grown by Atomic Layer Deposition. Journal of Electronic Materials, 2018, 47, 6709-6715.	2.2	25
13	Tailoring the Band Alignment of Ga <sub>x</sub> Zn <sub>1-x</sub> O/InGaZnO Heterojunction for Modulation-Doped Transistor Applications. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800332.	1.8	4
14	Band alignment and interfacial chemical structure of the HfLaO/InGaZnO4 heterojunction investigated by x-ray photoelectron spectroscopy. Journal Physics D: Applied Physics, 2017, 50, 145106.	2.8	2
15	Determination of the Band Alignment of aâ€IGZO/aâ€IGMO Heterojunction for Highâ€Electron Mobility Transistor Application. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700251.	2.4	7
16	Ultrahigh-Responsivity, Rapid-Recovery, Solar-Blind Photodetector Based on Highly Nonstoichiometric Amorphous Gallium Oxide. ACS Photonics, 2017, 4, 2203-2211.	6.6	254
17	Novel AlN/Pt/ZnO Electrode for High Temperature SAW Sensors. Materials, 2017, 10, 69.	2.9	14
18	Amorphous InGaMgO Ultraviolet Photo-TFT with Ultrahigh Photosensitivity and Extremely Large Responsivity. Materials, 2017, 10, 168.	2.9	6

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19	Improvement of High-Temperature Stability of Al2O3/Pt/ZnO/Al2O3 Film Electrode for SAW Devices by Using Al2O3 Barrier Layer. Materials, 2017, 10, 1377.	2.9	17
20	PMN-PT/PVDF Nanocomposite for High Output Nanogenerator Applications. Nanomaterials, 2016, 6, 67.	4.1	34
21	The Characterization of Surface Acoustic Wave Devices Based on AlN-Metal Structures. Sensors, 2016, 16, 526.	3.8	34
22	Effects of AlN Coating Layer on High Temperature Characteristics of Langasite SAW Sensors. Sensors, 2016, 16, 1436.	3.8	20
23	Effects of the magnesium oxide thin films' microstructures on the residual stresses. Journal of Alloys and Compounds, 2016, 679, 122-124.	5.5	3
24	High temperature characteristics of AlN film SAW sensor integrated with TC4 alloy substrate. Sensors and Actuators A: Physical, 2016, 249, 57-61.	4.1	10
25	Electrical performance of alumina films made in EB evaporation. Modern Physics Letters B, 2016, 30, 1650260.	1.9	1
26	Surfactant-Assisted Hydrothermal Synthesis of PMN-PT Nanorods. Nanoscale Research Letters, 2016, 11, 49.	5.7	6
27	AlN-based surface acoustic wave resonators on platinum bottom electrodes for high-temperature sensing applications. Rare Metals, 2016, 35, 408-411.	7.1	26
28	AlN-based surface acoustic wave resonators for temperature sensing applications. Materials Express, 2015, 5, 367-370.	0.5	29
29	High-Temperature SAW Wireless Strain Sensor with Langasite. Sensors, 2015, 15, 28531-28542.	3.8	51
30	Dielectric thin films for GaN-based high-electron-mobility transistors. Rare Metals, 2015, 34, 371-380.	7.1	3
31	AIN film SAW resonator integrated with metal structure. Electronics Letters, 2015, 51, 379-380.	1.0	11
32	Nano-structured optical hetero-coatings for ultraviolet protection. Materials Letters, 2015, 152, 290-292.	2.6	3
33	RESIDUAL STRESSES IN OBLIQUE INCIDENCE DEPOSITED ALUMINA THIN FILM. Surface Review and Letters, 2014, 21, 1450024.	1.1	1
34	Polymer assisted thick single-layer YBa2Cu3O7-δ films prepared with modified TFA-MOD method. Rare Metals, 2014, 33, 594-597.	7.1	5
35	Growth characteristics and device properties of MOD derived $\hat{I}^2$ -Ga2O3 films. Journal of Materials Science: Materials in Electronics, 2014, 25, 3629-3632.	2.2	18
36	The electrical and morphological properties of magnesium oxide/alumina bilayered thin films prepared by electron beam evaporation at oblique incidence. Applied Surface Science, 2014, 292, 665-669.	6.1	5

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37	The optical properties of alumina films prepared by electron beam evaporation at oblique incidence. Materials Letters, 2013, 101, 1-4.	2.6	14
38	AlN-based piezoelectric micromachined ultrasonic transducer for photoacoustic imaging. Applied Physics Letters, $2013,103,103$	3.3	59
39	Comparative study on the doping effect of 3d elements in Bi1.5Pb0.2Sr2Ca2Cu2.8M0.2O y (M=Sc, Ti, V,) Tj ETC	9q1_1_0.78	43] 4 rgBT <mark> </mark> O
40	Highly orientated Bi(Pb)SrCaCuO superconducting thin film by magnetron sputtering of three targets. Journal of Materials Science Letters, 1996, 15, 531-533.	0.5	0